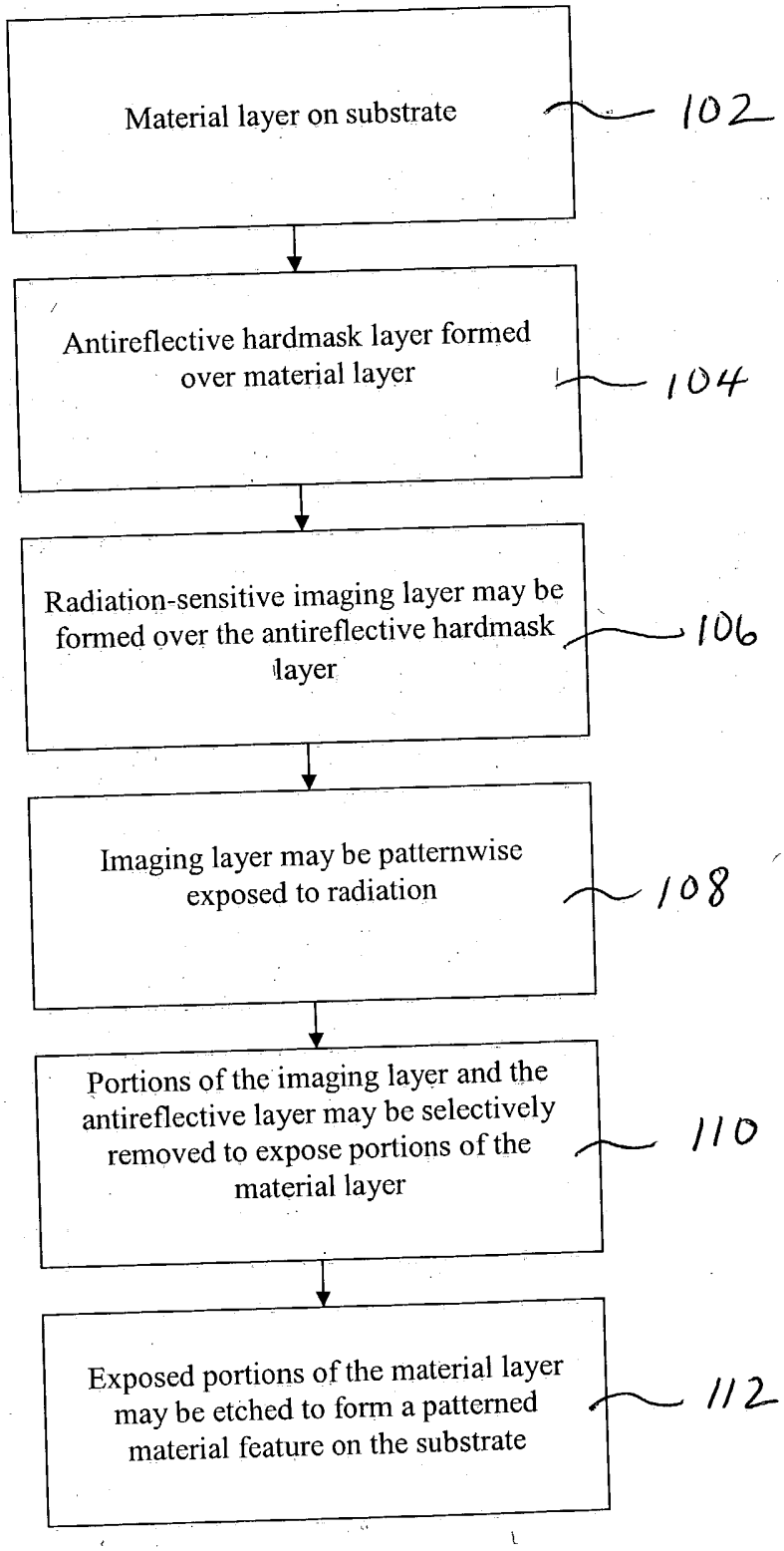
Material layer on substrate
102
Antireflective hardmask layer formed over material layer
104
Radiation-sensitive imaging layer may be formed over the antireflective hardmask layer
106
Imaging layer may be patternwise exposed to radiation
108
Portions of the imaging layer and the antireflective layer may be selectively removed to expose portions of the material layer
110
Exposed portions of the material layer may be etched to form a patterned material feature on the substrate
112

FIG. 1